



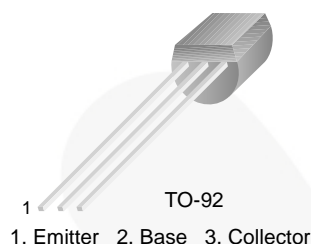
November 2014

# SS8550

## PNP Epitaxial Silicon Transistor

### Features

- 2 W Output Amplifier of Portable Radios in Class B Push-pull Operation.
- Complimentary to SS8050
- Collector Current:  $I_C = 1.5\text{ A}$



### Ordering Information

Part Number	Top Mark	Package	Packing Method
SS8550BBU	S8550	TO-92 3L	Bulk
SS8550CBU	S8550	TO-92 3L	Bulk
SS8550CTA	S8550	TO-92 3L	Ammo
SS8550DBU	S8550	TO-92 3L	Bulk
SS8550DTA	S8550	TO-92 3L	Ammo

### Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current	-1.5	A
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-65 to 150	$^\circ\text{C}$

**Thermal Characteristics<sup>(1)</sup>**

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$P_D$	Power Dissipation	1	W
	Derate Above $25^\circ\text{C}$	8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	$^\circ\text{C}/\text{W}$

**Note:**

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

**Electrical Characteristics**

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -100\ \mu\text{A}$ , $I_E = 0$	-40			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -2\ \text{mA}$ , $I_B = 0$	-25			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -100\ \mu\text{A}$ , $I_C = 0$	-6			V
$I_{CBO}$	Collector Cut-Off Current	$V_{CB} = -35\ \text{V}$ , $I_E = 0$			-100	nA
$I_{EBO}$	Emitter Cut-Off Current	$V_{EB} = -6\ \text{V}$ , $I_C = 0$			-100	nA
$h_{FE1}$	DC Current Gain	$V_{CE} = -1\ \text{V}$ , $I_C = -5\ \text{mA}$	45	170		
$h_{FE2}$		$V_{CE} = -1\ \text{V}$ , $I_C = -100\ \text{mA}$	85	160	300	
$h_{FE3}$		$V_{CE} = -1\ \text{V}$ , $I_C = -800\ \text{mA}$	40	80		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -800\ \text{mA}$ , $I_B = -80\ \text{mA}$		-0.28	-0.50	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -800\ \text{mA}$ , $I_B = -80\ \text{mA}$		-0.98	-1.20	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = -1\ \text{V}$ , $I_C = -10\ \text{mA}$		-0.66	-1.00	V
$C_{ob}$	Output Capacitance	$V_{CB} = -10\ \text{V}$ , $I_E = 0$ , $f = 1\ \text{MHz}$		15		pF
$f_T$	Current Gain Bandwidth Product	$V_{CE} = -10\ \text{V}$ , $I_C = -50\ \text{mA}$	100	200		MHz

 **$h_{FE}$  Classification**

Classification	B	C	D
$h_{FE2}$	85 ~ 160	120 ~ 200	160 ~ 300

## Typical Performance Characteristics

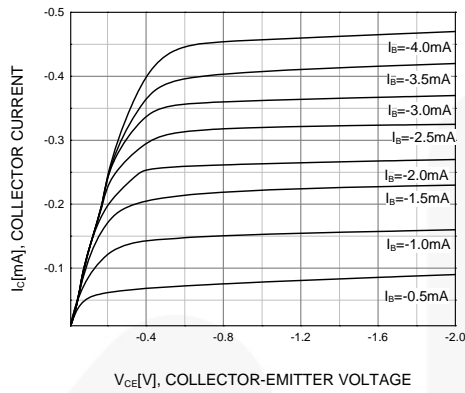


Figure 1. Static Characteristic

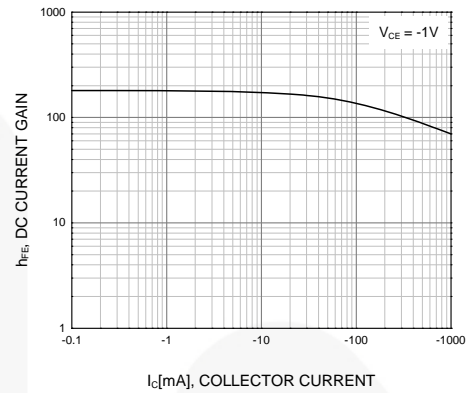


Figure 2. DC Current Gain

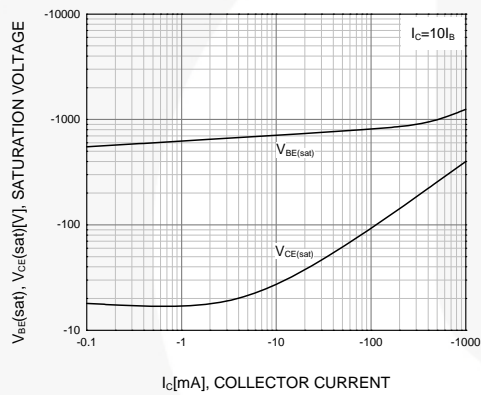


Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

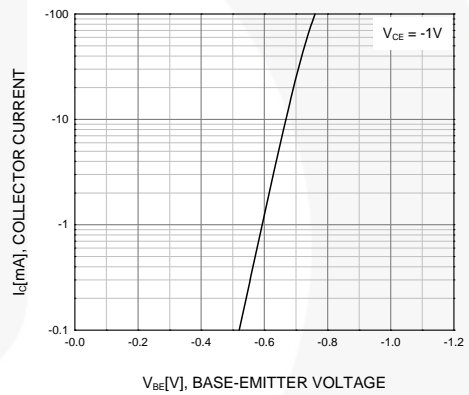


Figure 4. Base-Emitter On Voltage

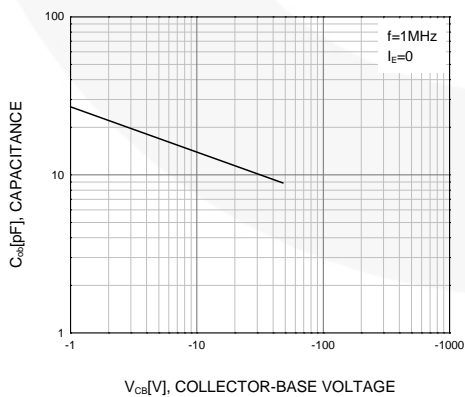


Figure 5. Collector Output Capacitance

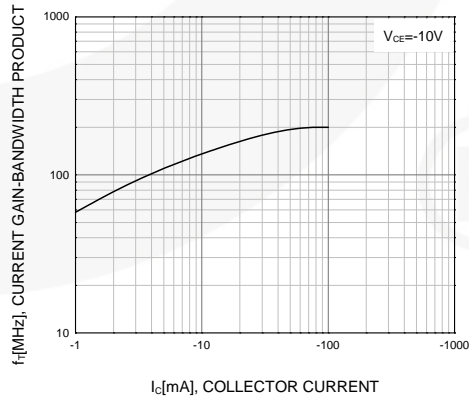
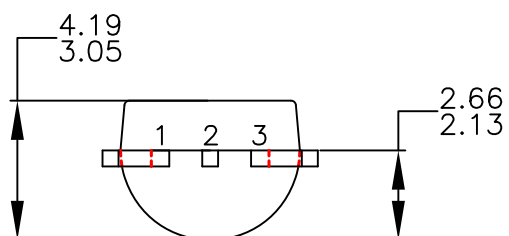
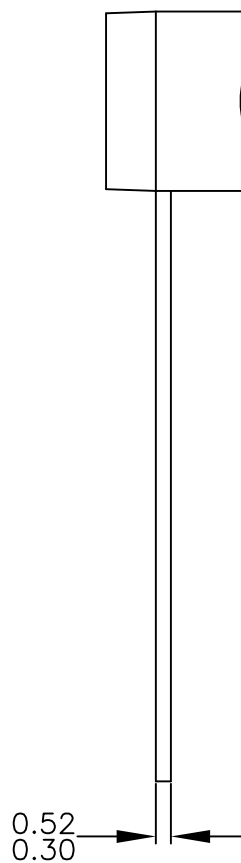
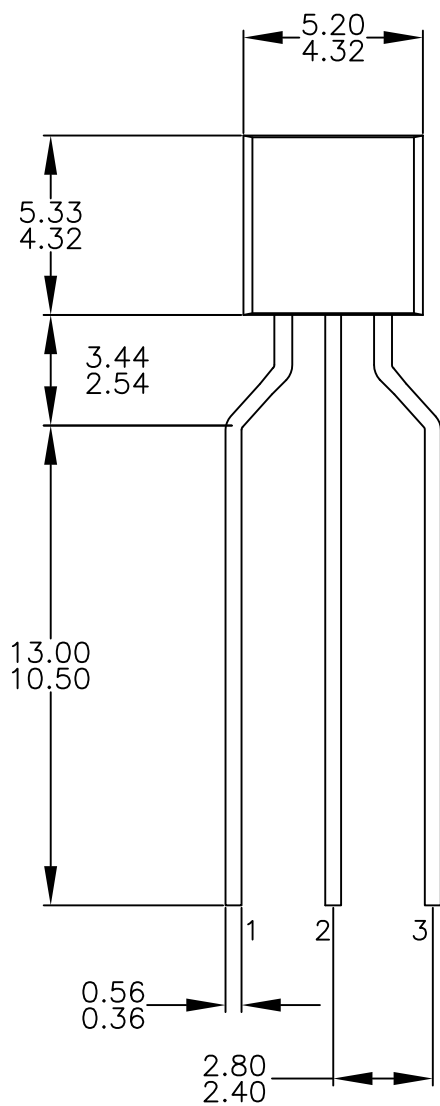


Figure 6. Current Gain Bandwidth Product

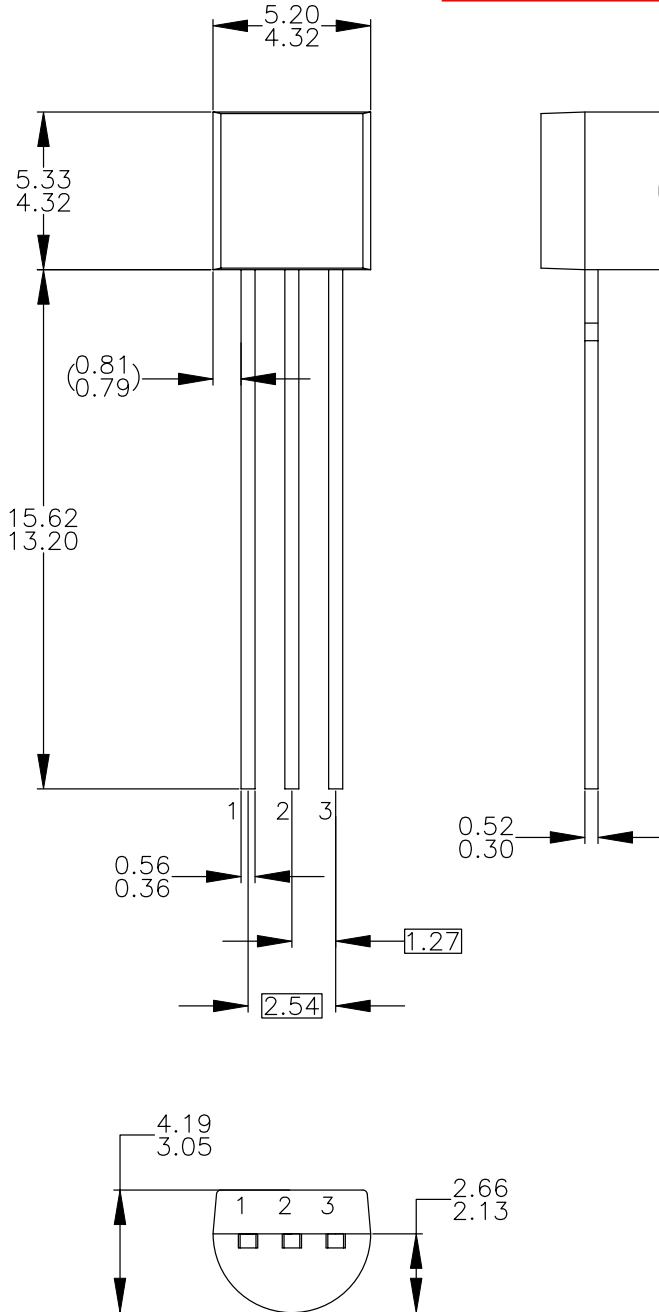


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- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
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**APPROVED**  
July-14-2008



REVISIONS			
NO.	DESCRIPTION	DATE	NAME/SITE
A	RELEASE TO DOCUMENT CONTROL	MAR.4'96	RP
B	RDRW AS PER STD DWG TEMPLATE. CHG DIM REF FR DUAL DIM INCH(MM) TO SINGLE DIM MM. CHG LD PITCH DIM FR 1.14-1.40 TO 1.27 BSC. ADD DIM 2.54 BSC. CHG PKG WIDTH DIM FR 4.32- 4.70 TO 4.32-4.83; CHG PKG HEIGHT DIM FR 4.32-4.70 TO 4.32-4.78; CHG LD THICK DIM FR 0.30- 0.48 TO 0.30-0.52; DAMBAR-PKG DIM FR 1.27-1.65 TO 0.90-1.65; LD LGH DIM FR 14.47-15.64 TO 14.47-15.62; PKG DIM: 1.02-1.52 TO 0.92-1.52, 3.61-4.45 TO 3.40-4.80; NOTE 2: ADD DMOS "M" OPT'N AND LEGEND; NOTE B PKG 94 JFET OPT'N: CHG D TO S, CHG S TO D. ADD NOTE C: MOVE NOTE B INFO FR PKG 97&98 TO NEW NOTE D.	4OCT1999	RCM/MRG
3	CHG LD LEN FR 13.81 TO 13.88; CHG MOLD BODY HT FR 4.33 TO 4.32; CHG PKG EDGE TO LD EDGE DIST FR (0.81) TO (0.79); CHG MOLD BODY WIDTH FR 4.33 TO 4.32; ADD PKG THICKNESS DIM "E"; CHG "S" DIM FR 2.13 TO 2.16; REMOVE DAMBAR & EJECTOR PIN LOCATOR FEATURES & DIMENSIONS; REMOVE MOLDED SURFACE & DRAFT ANGLE DIMS; ADD NOTE ON JEDEC REFERENCE; ADD NOTE ON ASME Y14.5M-1994; REMOVE NOTE ON L34Z OPTION; ADD NOTE ON DWG FILENAME.	12FEB08	BMR/FSCP

NOTES: UNLESS OTHERWISE SPECIFIED

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B) ALL DIMENSIONS ARE IN MILLIMETERS.  
C) DRAWING CONFORMS TO ASME Y14.5M-1994.  
D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92			94			96			97			98		
	P	F	M	P	F	M	B	F	M	P	F	M	P	F	M
1	E	S	S	E	S	S	B	D	G	C	G	D	C	G	D
2	B	D	G	C	G	D	E	S	S	B	D	G	E	S	S
3	C	G	D	B	D	G	C	G	D	E	S	S	B	D	G

LEGEND:

P - BIPOLAR E - EMITTER D - DRAIN  
F - JFET B - BASE S - SOURCE  
M - DMOS C - COLLECTOR G - GATE

- E) FOR PACKAGE 92, 94, 96, 97 AND 98:  
PIN CONFIGURATION DRAIN "D" AND SOURCE "S"  
ARE INTERCHANGEABLE AT JFET "F" OPTION.  
F) DRAWING FILENAME: MKT-ZA03DREV3.

APPROVALS	DATE	<b>FAIRCHILD</b> SEMICONDUCTOR™		
DRAWN: J.U. COMPARATIVO JR.	03APR2008			
CHECKED: L. GALERA				
APPROVED: M.R. GESTOLE				
G.S. BAJE		3LD, TO-92, MOLDED STD STRAIGHT LD (NO EOL CODE)		
PROJECTION	SCALE	SIZE	DRAWING NUMBER	REV
	1:1	N/A	MKT-ZA03D	3
INCH (MM)	FORMERLY: N/A			SHEET : 1 OF 1



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